



PJA3416A

20V N-Channel Enhancement Mode MOSFET

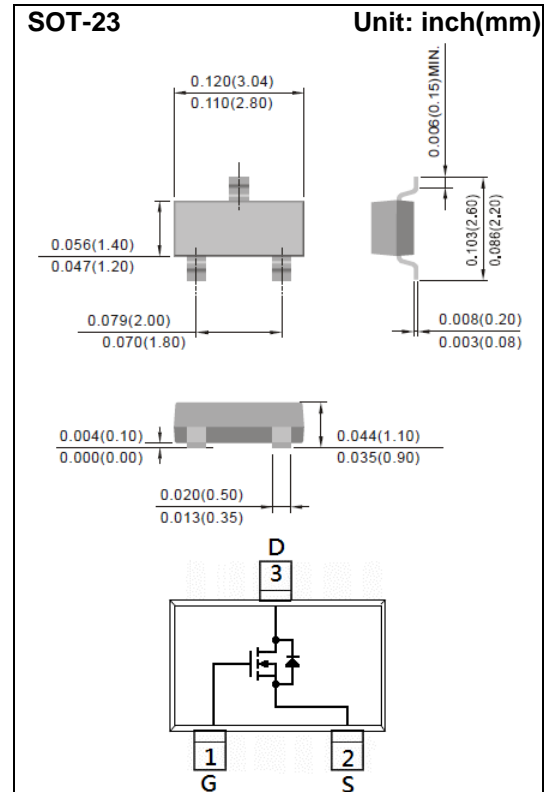
Voltage 20 V **Current** 5.8A

Features

- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_D@5.8A < 24m\Omega$
- $R_{DS(ON)}$, $V_{GS}@2.5V$, $I_D@3.2A < 30m\Omega$
- $R_{DS(ON)}$, $V_{GS}@1.8V$, $I_D@1.6A < 42m\Omega$
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc..
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : SOT-23 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0003 ounces, 0.0084 grams



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	+12	V
Continuous Drain Current	I_D	5.8	A
Pulsed Drain Current	I_{DM}	23.2	A
Power Dissipation	P_D	$T_a=25^\circ C$	1.25
		Derate above $25^\circ C$	10
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~150	$^\circ C$
Typical Thermal Resistance	$R_{\theta JA}$	100	$^\circ C/W$
- Junction to Ambient ^(Note 3)			



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Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	20	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	0.5	0.68	1.2	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =5.8A	-	20	24	mΩ
		V _{GS} =2.5V, I _D =3.2A	-	25	30	
		V _{GS} =1.8V, I _D =1.6A	-	32	42	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V	-	-	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±12V, V _{DS} =0V	-	-	±100	nA
Dynamic (Note 5)						
Total Gate Charge	Q _g	V _{DS} =10V, I _D =5.8A, V _{GS} =4.5V(Note 1,2)	-	10.4	-	nC
Gate-Source Charge	Q _{gs}		-	0.8	-	
Gate-Drain Charge	Q _{gd}		-	3.2	-	
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0V, f=1.0MHZ	-	592	-	pF
Output Capacitance	C _{oss}		-	91	-	
Reverse Transfer Capacitance	C _{rss}		-	82	-	
Turn-On Delay Time	t _{d(on)}	V _{DD} =10V, I _D =5.8A, V _{GS} =4.5V, R _G =6Ω(Note 1,2)	-	4.3	-	ns
Turn-On Rise Time	t _r		-	39	-	
Turn-Off Delay Time	t _{d(off)}		-	31	-	
Turn-Off Fall Time	t _f		-	30	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I _S	---	-	-	1.5	A
Diode Forward Voltage	V _{SD}	I _S =1.0A, V _{GS} =0V	-	0.76	1.2	V

NOTES :

1. Pulse width ≤ 300us, Duty cycle ≤ 2%
2. Essentially independent of operating temperature typical characteristics.
3. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper
4. The maximum current rating is package limited
5. Guaranteed by design, not subject to production testing



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TYPICAL CHARACTERISTIC CURVES

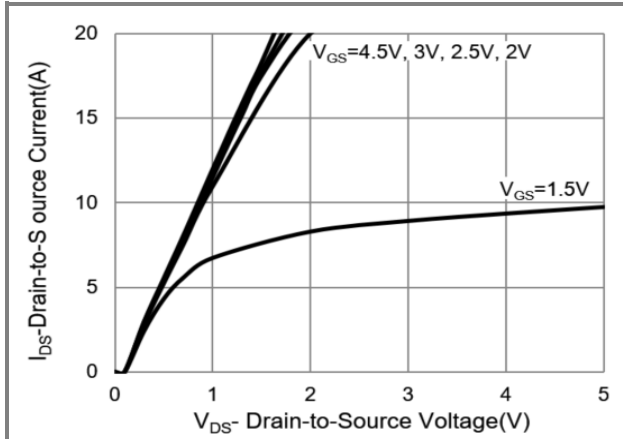


Fig.1 On-Region Characteristics

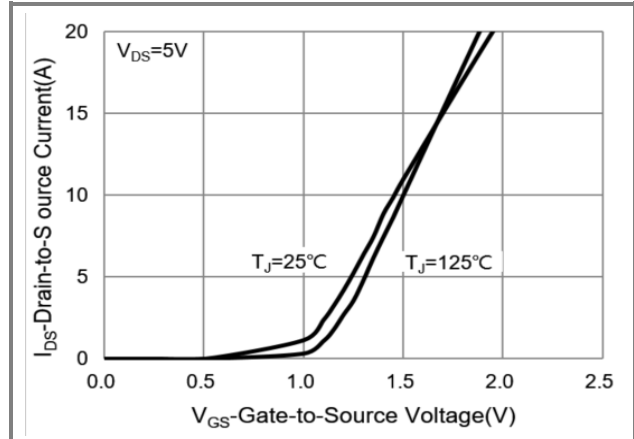


Fig.2 Transfer Characteristics

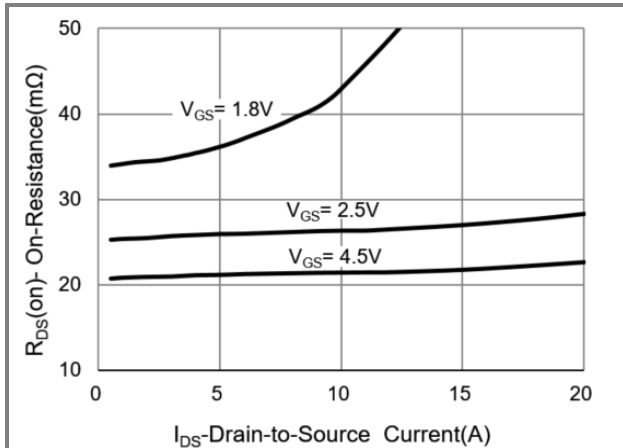


Fig.3 On-Resistance vs. Drain Current

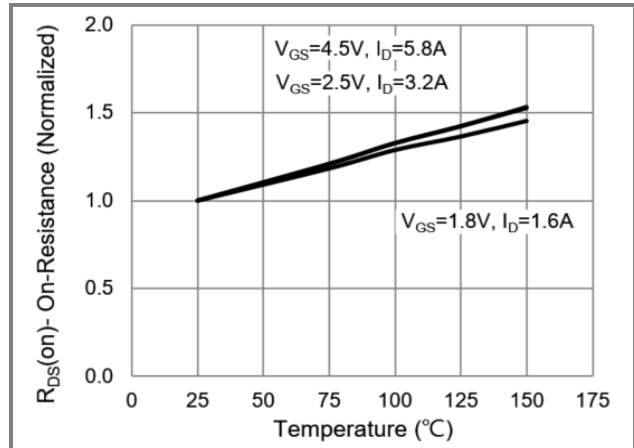


Fig.4 On-Resistance vs. Junction temperature

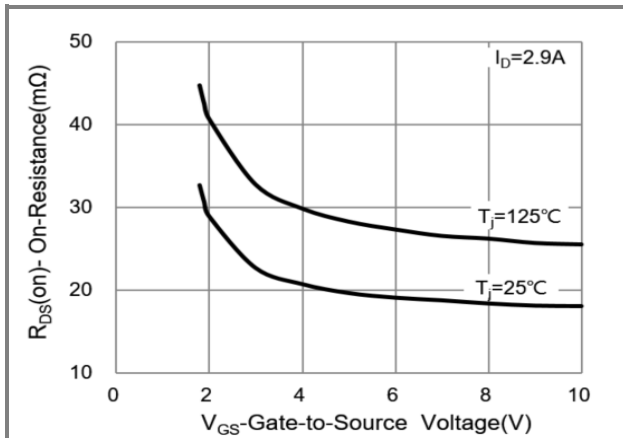


Fig.5 On-Resistance Variation with VGS.

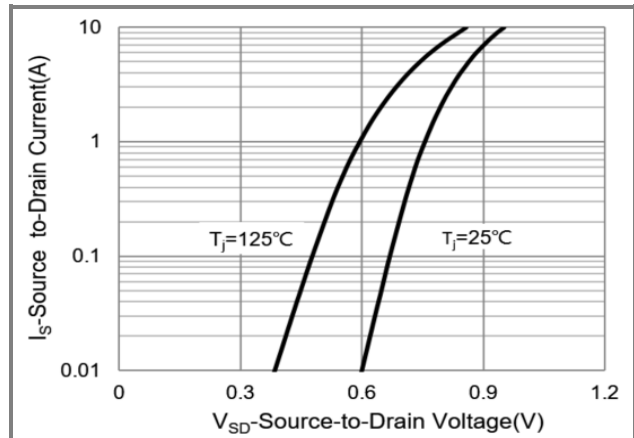


Fig.6 Body Diode Characteristics



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TYPICAL CHARACTERISTIC CURVES

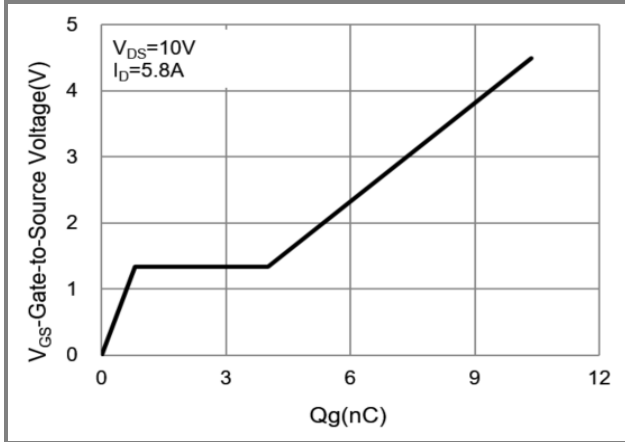


Fig.7 Gate-Charge Characteristics

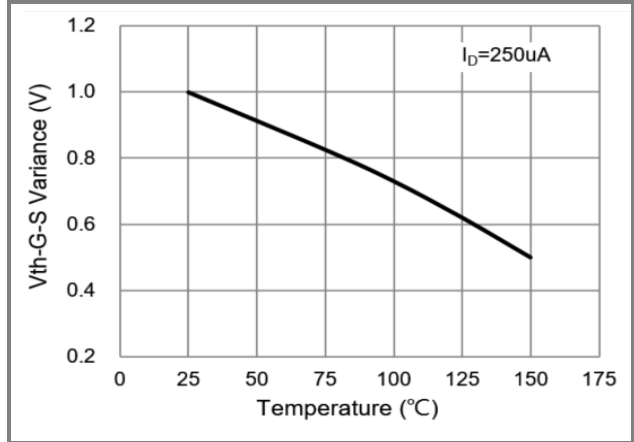


Fig.8 Threshold Voltage Variation with Temperature.

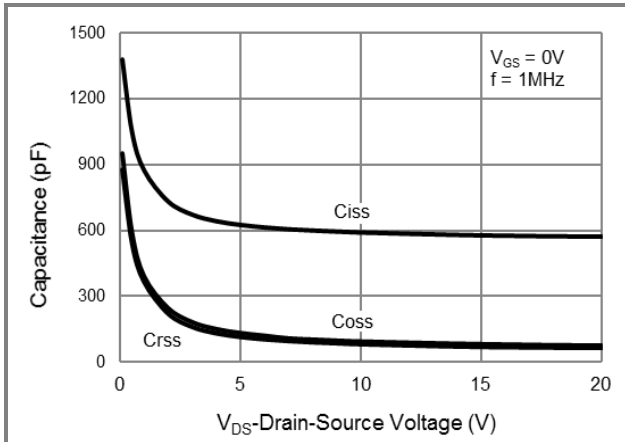


Fig.9 Capacitance vs. Drain-Source Voltage.



PJA3416A

PART NO. PACKING CODE VERSION

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJA3416A_R1_00001	SOT-23	3K pcs / 7" reel	A6A	Halogen free RoHS compliant
PJA3416A_R2_00001	SOT-23	12K pcs / 13" reel	A6A	Halogen free RoHS compliant

MOUNTING PAD LAYOUT

